Nguyen Tien Son

List of Publications by Year in Descending Order

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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

226 papers	6,162 citations	41 h-index	69 g-index
238 ext. papers	7,050 ext. citations	3.4 avg, IF	5.42 L-index

#	Paper	IF	Citations
226	Broadband single-mode planar waveguides in monolithic 4H-SiC. *Journal of Applied Physics*, **2022**, 131, 025703	2.5	1
225	Five-second coherence of a single spin with single-shot readout in silicon carbide.. *Science Advances*, **2022**, 8, eabm5912	14.3	9
224	Electromagnetically induced transparency in inhomogeneously broadened divacancy defect ensembles in SiC. *Journal of Applied Physics*, **2022**, 131, 094401	2.5	1
223	Fabrication and nanophotonic waveguide integration of silicon carbide colour centres with preserved spin-optical coherence. *Nature Materials*, **2021**,	27	11
222	Narrow inhomogeneous distribution of spin-active emitters in silicon carbide. *Applied Physics Letters*, **2021**, 118, 144003	3.4	3
221	Charge state control of the silicon vacancy and divacancy in silicon carbide. *Journal of Applied Physics*, **2021**, 129, 215702	2.5	4
220	Towards identification of silicon vacancy-related electron paramagnetic resonance centers in 4H-SiC. *Physical Review B*, **2021**, 104,	3.3	4
219	Deep levels related to the carbon antisite□vacancy pair in 4H-SiC. *Journal of Applied Physics*, **2021**, 130, 065703	2.5	3
218	Vibronic States and Their Effect on the Temperature and Strain Dependence of Silicon-Vacancy Qubits in 4H-SiC. *Physical Review Applied*, **2020**, 13,	4.3	29
217	Developing silicon carbide for quantum spintronics. *Applied Physics Letters*, **2020**, 116, 190501	3.4	45
216	Spin-controlled generation of indistinguishable and distinguishable photons from silicon vacancy centres in silicon carbide. *Nature Communications*, **2020**, 11, 2516	17.4	24
215	Spin-relaxation times exceeding seconds for color centers with strong spin□orbit coupling in SiC. *New Journal of Physics*, **2020**, 22, 103051	2.9	7
214	Spectrally reconfigurable quantum emitters enabled by optimized fast modulation. *Npj Quantum Information*, **2020**, 6,	8.6	15
213	Electron paramagnetic resonance and theoretical study of gallium vacancy in □Ga2O3. *Applied Physics Letters*, **2020**, 117, 032101	3.4	19
212	Entanglement and control of single nuclear spins in isotopically engineered silicon carbide. *Nature Materials*, **2020**, 19, 1319-1325	27	40
211	Electrical Charge State Manipulation of Single Silicon Vacancies in a Silicon Carbide Quantum Optoelectronic Device. *Nano Letters*, **2019**, 19, 7173-7180	11.5	36
210	Energy levels and charge state control of the carbon antisite-vacancy defect in 4H-SiC. *Applied Physics Letters*, **2019**, 114, 212105	3.4	11

209	High-fidelity spin and optical control of single silicon-vacancy centres in silicon carbide. *Nature Communications*, **2019**, 10, 1954	17.4	99
208	Identification of divacancy and silicon vacancy qubits in 6H-SiC. *Applied Physics Letters*, **2019**, 114, 112107	3.4	15
207	Ligand hyperfine interactions at silicon vacancies in 4H-SiC. *Journal of Physics Condensed Matter*, **2019**, 31, 195501	1.8	9
206	Optical Properties of Vanadium in 4H Silicon Carbide for Quantum Technology. *Physical Review Applied*, **2019**, 12,	4.3	32
205	First-Principles Study on Photoluminescence Quenching of Divacancy in 4H SiC. *Materials Science Forum*, **2019**, 963, 714-717	0.4	1
204	Electrical and optical control of single spins integrated in scalable semiconductor devices. *Science*, **2019**, 366, 1225-1230	33.3	88
203	Stabilization of point-defect spin qubits by quantum wells. *Nature Communications*, **2019**, 10, 5607	17.4	28
202	Coherent electrical readout of defect spins in silicon carbide by photo-ionization at ambient conditions. *Nature Communications*, **2019**, 10, 5569	17.4	24
201	First principles predictions of magneto-optical data for semiconductor point defect identification: the case of divacancy defects in 4H-SiC. *New Journal of Physics*, **2018**, 20, 023035	2.9	25
200	Quantum Properties of Dichroic Silicon Vacancies in Silicon Carbide. *Physical Review Applied*, **2018**, 9,	4.3	65
199	Bright single photon sources in lateral silicon carbide light emitting diodes. *Applied Physics Letters*, **2018**, 112, 231103	3.4	21
198	Excitation properties of the divacancy in 4H-SiC. *Physical Review B*, **2018**, 98,	3.3	33
197	Identification and tunable optical coherent control of transition-metal spins in silicon carbide. *Npj Quantum Information*, **2018**, 4,	8.6	35
196	Ab Initio Theory of Si-Vacancy Quantum Bits in 4H and 6H-SiC. *Materials Science Forum*, **2018**, 924, 895-900	0.4	1
195	Scalable Quantum Photonics with Single Color Centers in Silicon Carbide. *Nano Letters*, **2017**, 17, 1782-1786	11.5	85
194	Resonant optical spectroscopy and coherent control of Cr4+ spin ensembles in SiC and GaN. *Physical Review B*, **2017**, 95,	3.3	42
193	Identification of Si-vacancy related room-temperature qubits in 4H silicon carbide. *Physical Review B*, **2017**, 96,	3.3	51
192	Isolated Spin Qubits in SiC with a High-Fidelity Infrared Spin-to-Photon Interface. *Physical Review X*, **2017**, 7,	9.1	78

191	Stark tuning and electrical charge state control of single divacancies in silicon carbide. *Applied Physics Letters*, **2017**, 111, 262403	3.4	51
190	Scalable Quantum Photonics with Single Color Centers in Silicon Carbide **2017**,		2
189	n-Type conductivity bound by the growth temperature: the case of Al0.72Ga0.28N highly doped by silicon. *Journal of Materials Chemistry C*, **2016**, 4, 8291-8296	7.1	4
188	Vector Magnetometry Using Silicon Vacancies in 4H-SiC Under Ambient Conditions. *Physical Review Applied*, **2016**, 6,	4.3	52
187	Electronic properties of defects in high-fluence electron-irradiated bulk GaN. *Physica Status Solidi (B): Basic Research*, **2016**, 253, 521-526	1.3	3
186	Electronic properties of Si-doped Alx Ga1−xN with aluminum mole fractions above 80%. *Journal of Applied Physics*, **2016**, 120, 145702	2.5	34
185	Deep levels in as-grown and electron-irradiated n-type GaN studied by deep level transient spectroscopy and minority carrier transient spectroscopy. *Journal of Applied Physics*, **2016**, 119, 095707	2.5	7
184	Donor and double-donor transitions of the carbon vacancy related EH6/7 deep level in 4H-SiC. *Journal of Applied Physics*, **2016**, 119, 235703	2.5	12
183	Electronic properties of the residual donor in unintentionally doped β-Ga2O3. *Journal of Applied Physics*, **2016**, 120, 235703	2.5	44
182	On the behavior of silicon donor in conductive AlxGa1−xN (0.63≤x≤1). *Physica Status Solidi (B): Basic Research*, **2015**, 252, 1306-1310	1.3	8
181	Conjugated Polyelectrolyte Blends for Electrochromic and Electrochemical Transistor Devices. *Chemistry of Materials*, **2015**, 27, 6385-6393	9.6	67
180	Isolated electron spins in silicon carbide with millisecond coherence times. *Nature Materials*, **2015**, 14, 160-3	27	278
179	Coherent control of single spins in silicon carbide at room temperature. *Nature Materials*, **2015**, 14, 164-8	27	347
178	Optical properties and Zeeman spectroscopy of niobium in silicon carbide. *Physical Review B*, **2015**, 92,	3.3	5
177	Exciton luminescence in AlN triggered by hydrogen and thermal annealing. *Applied Physics Letters*, **2015**, 106, 242101	3.4	9
176	Shallow donor in natural MoS2. *Physica Status Solidi - Rapid Research Letters*, **2015**, 9, 707-710	2.5	5
175	Theoretical and electron paramagnetic resonance studies of hyperfine interaction in nitrogen doped 4H and 6H SiC. *Journal of Applied Physics*, **2014**, 115, 073705	2.5	16
174	Hydrogen at zinc vacancy of ZnO: An EPR and ESEEM study **2014**,		4

173	Quantitative comparison between Z1⁄2 center and carbon vacancy in 4H-SiC. *Journal of Applied Physics*, **2014**, 115, 143705	2.5	33
172	Stable and metastable Si negative-U centers in AlGaN and AlN. *Applied Physics Letters*, **2014**, 105, 162106	3.4	41
171	Radiation-induced defects in GaN bulk grown by halide vapor phase epitaxy. *Applied Physics Letters*, **2014**, 105, 102103	3.4	17
170	Characterization of the nitrogen split interstitial defect in wurtzite aluminum nitride using density functional theory. *Journal of Applied Physics*, **2014**, 116, 113702	2.5	5
169	High-Resolution Raman and Luminescence Spectroscopy of Isotope-Pure 28Si12C, Natural and 13C Enriched 4H-SiC. *Materials Science Forum*, **2014**, 778-780, 471-474	0.4	9
168	Identification of the Negative Carbon Vacancy at Quasi-Cubic Site in 4H-SiC by EPR and Theoretical Calculations. *Materials Science Forum*, **2014**, 778-780, 285-288	0.4	
167	Electronic Defects in Electron-Irradiated Silicon Carbide and III-Nitrides **2014**, 417-451		
166	Negative-U carbon vacancy in 4H-SiC: Assessment of charge correction schemes and identification of the negative carbon vacancy at the quasicubic site. *Physical Review B*, **2013**, 88,	3.3	39
165	Negative-U behavior of the Si donor in Al0.77Ga0.23N. *Applied Physics Letters*, **2013**, 103, 042101	3.4	8
164	Optical Properties of the Niobium Centre in 4H, 6H, and 15R SiC. *Materials Science Forum*, **2013**, 740-742, 405-408	0.4	1
163	Electron Paramagnetic Resonance Studies of Nb in 6H-SiC. *Materials Science Forum*, **2013**, 740-742, 385-388	0.4	
162	Silicon and Oxygen in High-Al-Content AlGaN: Incorporation Kinetics and Electron Paramagnetic Resonance Study. *Solid State Phenomena*, **2013**, 205-206, 441-445	0.4	2
161	Magnetic resonance identification of hydrogen at a zinc vacancy in ZnO. *Journal of Physics Condensed Matter*, **2013**, 25, 335804	1.8	12
160	The complex impact of silicon and oxygen on the n-type conductivity of high-Al-content AlGaN. *Applied Physics Letters*, **2013**, 102, 132113	3.4	28
159	Investigation on origin of Z1/2 center in SiC by deep level transient spectroscopy and electron paramagnetic resonance. *Applied Physics Letters*, **2013**, 102, 112106	3.4	44
158	Optical identification and electronic configuration of tungsten in 4H- and 6H-SiC. *Physica B: Condensed Matter*, **2012**, 407, 1462-1466	2.8	12
157	Negative-U system of carbon vacancy in 4H-SiC. *Physical Review Letters*, **2012**, 109, 187603	7.4	176
156	Electronic Configuration of Tungsten in 4H-, 6H-, and 15R-SiC. *Materials Science Forum*, **2012**, 717-720, 211-216	0.4	

155	Identification of Niobium in 4H-SiC by EPR and Ab Initio Studies. *Materials Science Forum*, **2012**, 717-720, 217-220	0.4	3
154	Electron paramagnetic resonance and theoretical studies of Nb in 4H- and 6H-SiC. *Journal of Applied Physics*, **2012**, 112, 083711	2.5	10
153	Transition Metal Defects in Cubic and Hexagonal Polytypes of SiC: Site Selection, Magnetic and Optical Properties from Ab Initio Calculations. *Materials Science Forum*, **2012**, 717-720, 205-210	0.4	2
152	Asymmetric split-vacancy defects in SiC polytypes: a combined theoretical and electron spin resonance study. *Physical Review Letters*, **2011**, 107, 195501	7.4	22
151	Silicon in AlN: shallow donor and DX behaviors. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2011**, 8, 2167-2169		7
150	Defects at nitrogen site in electron-irradiated AlN. *Applied Physics Letters*, **2011**, 98, 242116	3.4	8
149	Shallow donor and DX states of Si in AlN. *Applied Physics Letters*, **2011**, 98, 092104	3.4	41
148	The Carbon Vacancy Related EI4 Defect in 4H-SiC. *Materials Science Forum*, **2010**, 645-648, 399-402	0.4	1
147	Group-II acceptors in wurtzite AlN: A screened hybrid density functional study. *Applied Physics Letters*, **2010**, 96, 192110	3.4	33
146	Theory of Neutral Divacancy in SiC: A Defect for Spintronics. *Materials Science Forum*, **2010**, 645-648, 395-397	0.4	27
145	EPR and ab initio calculation study on the EI4 center in 4H- and 6H-SiC. *Physical Review B*, **2010**, 82,	3.3	10
144	Radiation-induced defects in GaN. *Physica Scripta*, **2010**, T141, 014015	2.6	4
143	The EI4 EPR centre in 6H SiC. *Physica Scripta*, **2010**, T141, 014013	2.6	
142	EPR and ENDOR Studies of Shallow Donors in SiC. *Applied Magnetic Resonance*, **2010**, 39, 49-85	0.8	9
141	Magnetic characterization of conductance electrons in GaN. *Physica Status Solidi (B): Basic Research*, **2010**, 247, 1728-1731	1.3	5
140	Identification of the gallium vacancy–oxygen pair defect in GaN. *Physical Review B*, **2009**, 80,	3.3	40
139	Defects Introduced by Electron-Irradiation at Low Temperatures in SiC. *Materials Science Forum*, **2009**, 615-617, 377-380	0.4	2
138	Photo-EPR Studies on Low-Energy Electron-Irradiated 4H-SiC. *Materials Science Forum*, **2009**, 615-617, 401-404	0.4	

137	The Silicon Vacancy in SiC. *Materials Science Forum*, **2009**, 615-617, 347-352	0.4	6
136	The silicon vacancy in SiC. *Physica B: Condensed Matter*, **2009**, 404, 4354-4358	2.8	70
135	Deep levels in low-energy electron-irradiated 4H-SiC. *Physica Status Solidi - Rapid Research Letters*, **2009**, 3, 121-123	2.5	9
134	Identification of a Frenkel-pair defect in electron-irradiated 3C SiC. *Physical Review B*, **2009**, 80,	3.3	10
133	Intrinsic Defects in HPSI 6H-SiC: an EPR Study. *Materials Science Forum*, **2008**, 600-603, 381-384	0.4	4
132	New Type of Defects Explored by Theory: Silicon Interstitial Clusters in SiC. *Materials Science Forum*, **2008**, 600-603, 413-416	0.4	
131	Deep Levels Responsible for Semi-Insulating Behavior in Vanadium-Doped 4H-SiC Substrates. *Materials Science Forum*, **2008**, 600-603, 401-404	0.4	0
130	EPR Identification of Defects and Impurities in SiC: To be Decisive. *Materials Science Forum*, **2008**, 600-603, 279-284	0.4	2
129	Electron paramagnetic resonance study on n-type electron-irradiated 3C-SiC. *Journal of Physics: Conference Series*, **2008**, 100, 042032	0.3	
128	Water adsorption on fullerene-like carbon nitride overcoats. *Thin Solid Films*, **2008**, 517, 1106-1110	2.2	33
127	EPR identification of intrinsic defects in SiC. *Physica Status Solidi (B): Basic Research*, **2008**, 245, 1298-1314	1.3	56
126	Common point defects in as-grown ZnO substrates studied by optical detection of magnetic resonance. *Journal of Crystal Growth*, **2008**, 310, 1006-1009	1.6	4
125	Prominent defects in semi-insulating SiC substrates. *Physica B: Condensed Matter*, **2007**, 401-402, 67-72	2.8	15
124	Magnetic resonance studies of defects in electron-irradiated ZnO substrates. *Physica B: Condensed Matter*, **2007**, 401-402, 507-510	2.8	2
123	Clustering of vacancy defects in high-purity semi-insulating SiC. *Physical Review B*, **2007**, 75,	3.3	24
122	Theoretical study of small silicon clusters in 4H-SiC. *Physical Review B*, **2007**, 76,	3.3	16
121	Deep levels and carrier compensation in V-doped semi-insulating 4H-SiC. *Applied Physics Letters*, **2007**, 91, 202111	3.4	10
120	Recombination centers in as-grown and electron-irradiated ZnO substrates. *Journal of Applied Physics*, **2007**, 102, 093504	2.5	17

119	Influence of Cooling Rate after High Temperature Annealing on Deep Levels in High-Purity Semi-Insulating 4H-SiC. *Materials Science Forum*, **2007**, 556-557, 371-374	0.4	2
118	A Theoretical Study on Aluminium-Related Defects in SiC. *Materials Science Forum*, **2007**, 556-557, 445-448	0.4	3
117	Deep Acceptor Levels of the Carbon Vacancy-Carbon Antisite Pairs in 4H-SiC. *Materials Science Forum*, **2007**, 556-557, 449-452	0.4	2
116	Intrinsic Defects in Semi-Insulating SiC: Deep Levels and their Roles in Carrier Compensation. *Materials Science Forum*, **2007**, 556-557, 465-468	0.4	3
115	Ab initio supercell calculations on aluminum-related defects in SiC. *Physical Review B*, **2007**, 75,	3.3	22
114	Defects and carrier compensation in semi-insulating 4H-SiC substrates. *Physical Review B*, **2007**, 75,	3.3	56
113	Identification of divacancies in 4H-SiC. *Physica B: Condensed Matter*, **2006**, 376-377, 334-337	2.8	4
112	Optical and morphological features of bulk and homoepitaxial ZnO. *Superlattices and Microstructures*, **2006**, 39, 247-256	2.8	10
111	Divacancy Model for P6/P7 Centers in 4H- and 6H-SiC. *Materials Science Forum*, **2006**, 527-529, 527-530	0.4	6
110	Divacancy and Its Identification: Theory. *Materials Science Forum*, **2006**, 527-529, 523-526	0.4	10
109	Characterization of Semi-insulating SiC. *Materials Research Society Symposia Proceedings*, **2006**, 911, 3		2
108	Shallow P Donors in 3C-, 4H- and 6H-SiC. *Materials Science Forum*, **2006**, 527-529, 593-596	0.4	1
107	Electron Paramagnetic Resonance Study of the HEI4/SI5 Center in 4H-SiC. *Materials Science Forum*, **2006**, 527-529, 543-546	0.4	6
106	Optical Studies of Deep Centers in Semi-Insulating SiC. *Materials Science Forum*, **2006**, 527-529, 455-460	0.4	1
105	Signature of the Negative Carbon Vacancy-Antisite Complex. *Materials Science Forum*, **2006**, 527-529, 539-542	0.4	3
104	Electron paramagnetic resonance and theoretical studies of shallow phosphorous centers in 3C-, 4H-, and 6H-SiC. *Physical Review B*, **2006**, 73,	3.3	29
103	Electrical characterization of metastable carbon clusters in SiC: A theoretical study. *Physical Review B*, **2006**, 73,	3.3	32
102	Intrinsic defects in high-purity SiC. *Microelectronic Engineering*, **2006**, 83, 130-134	2.5	14

101	Pulsed EPR studies of Phosphorus shallow donors in diamond and SiC. *Physica B: Condensed Matter*, **2006**, 376-377, 358-361	2.8	12
100	Identification of the carbon antisite-vacancy pair in 4H-SiC. *Physical Review Letters*, **2006**, 96, 145501	7.4	66
99	Divacancy in 4H-SiC. *Physical Review Letters*, **2006**, 96, 055501	7.4	151
98	Hyperfine Interaction of Nitrogen Donor in 4H-SiC Studied by Pulsed-ENDOR. *Materials Science Forum*, **2005**, 483-485, 351-354	0.4	1
97	Electron Paramagnetic Resonance of Shallow Phosphorous Centers in 4H- and 6H-SiC. *Materials Science Forum*, **2005**, 483-485, 515-518	0.4	5
96	Theoretical Investigations of Complexes of p-Type Dopants and Carbon Interstitial in SiC: Bistable, Negative-U Defects. *Materials Science Forum*, **2005**, 483-485, 519-522	0.4	5
95	Activation of shallow boron acceptor in CB coimplanted silicon carbide: A theoretical study. *Applied Physics Letters*, **2005**, 86, 102108	3.4	13
94	Possibility for the electrical activation of the carbon antisite by hydrogen in SiC. *Physical Review B*, **2005**, 71,	3.3	9
93	EPR and theoretical studies of negatively charged carbon vacancy in 4HSiC. *Physical Review B*, **2005**, 71,	3.3	53
92	Diffusion of hydrogen in perfect, p-type doped, and radiation-damaged 4HSiC. *Physical Review B*, **2004**, 69,	3.3	17
91	Hyperfine interaction of the nitrogen donor in 4HSiC. *Physical Review B*, **2004**, 70,	3.3	12
90	Annealing Behaviour of Vacancy-and Antisite-Related Defects in Electron-Irradiated 4H-SiC. *Materials Science Forum*, **2004**, 457-460, 473-476	0.4	9
89	Antisites as Possible Origin of Irradiation Induced Photoluminescence Centers in SiC: A Theoretical Study on Clusters of Antisites and Carbon Interstitials in 4H-SiC. *Materials Science Forum*, **2004**, 457-460, 443-448	0.4	1
88	EPR and theoretical studies of positively charged carbon vacancy in 4HSiC. *Physical Review B*, **2004** , 70,	3.3	43
87	Defects in High-Purity Semi-Insulating SiC. *Materials Science Forum*, **2004**, 457-460, 437-442	0.4	51
86	Electronic Structure of Deep Defects in SiC. *Advanced Texts in Physics*, **2004**, 461-492		7
85	Cyclotron Resonance Studies of Effective Masses and Band Structure in SiC. *Advanced Texts in Physics*, **2004**, 437-460		4
84	Defects in SiC. *Physica B: Condensed Matter*, **2003**, 340-342, 15-24	2.8	17

83	Anti-site pair in SiC: a model of the DI center. *Physica B: Condensed Matter*, **2003**, 340-342, 175-179	2.8	7
82	HTCVD Grown Semi-Insulating SiC Substrates. *Materials Science Forum*, **2003**, 433-436, 33-38	0.4	47
81	Correlation between the antisite pair and the DI center in SiC. *Physical Review B*, **2003**, 67,	3.3	66
80	Hydrogen passivation of nitrogen in SiC. *Applied Physics Letters*, **2003**, 83, 1385-1387	3.4	15
79	Defects in Semi-Insulating SiC Substrates. *Materials Science Forum*, **2003**, 433-436, 45-50	0.4	28
78	Calculation of Hyperfine Constants of Defects in 4H-SiC. *Materials Science Forum*, **2003**, 433-436, 511-514	0.4	14
77	Electrically active defects in n-type 4H-silicon carbide grown in a vertical hot-wall reactor. *Journal of Applied Physics*, **2003**, 93, 4708-4714	2.5	141
76	Silicon vacancy related TV2a center in 4H-SiC. *Physical Review B*, **2003**, 68,	3.3	17
75	Aggregation of carbon interstitials in silicon carbide: A theoretical study. *Physical Review B*, **2003**, 68,	3.3	94
74	Metastable defects in 6H-SiC: experiments and modeling. *Journal of Applied Physics*, **2002**, 91, 1324-1330	2.5	17
73	Photoexcitation-electron-paramagnetic-resonance studies of the carbon vacancy in 4H-SiC. *Applied Physics Letters*, **2002**, 81, 3945-3947	3.4	60
72	Hole effective masses in 6H-SiC from optically detected cyclotron resonance. *Physical Review B*, **2002**, 66,	3.3	11
71	Ligand hyperfine interaction at the neutral silicon vacancy in 4H- and 6H-SiC. *Physical Review B*, **2002**, 66,	3.3	39
70	Hole and Electron Effective Masses in 6H-SiC Studied by Optically Detected Cyclotron Resonance. *Materials Science Forum*, **2002**, 389-393, 525-528	0.4	1
69	Impurity-Controlled Dopant Activation - The Role of Hydrogen in p-Type Doping of SiC. *Materials Science Forum*, **2002**, 389-393, 561-564	0.4	3
68	The Neutral Silicon Vacancy in SiC: Ligand Hyperfine Interaction. *Materials Science Forum*, **2002**, 389-393, 501-504	0.4	8
67	Theoretical Investigation of an Intrinsic Defect in SiC. *Materials Science Forum*, **2002**, 389-393, 477-480	0.4	8
66	Passivation of p-type dopants in 4H-SiC by hydrogen. *Physica B: Condensed Matter*, **2001**, 308-310, 722-725	1.8	12

65	As-Grown and Process-Induced Intrinsic Deep-Level Luminescence in 4H-SiC. *Materials Science Forum*, **2001**, 353-356, 365-368	0.4	3
64	Boron Centers in 4H-SiC. *Materials Science Forum*, **2001**, 353-356, 455-458	0.4	18
63	Carbon vacancy-related defect in 4H and 6H SiC. *Physical Review B*, **2001**, 63,	3.3	93
62	Impurity-controlled dopant activation: Hydrogen-determined site selection of boron in silicon carbide. *Applied Physics Letters*, **2001**, 79, 2746-2748	3.4	25
61	Intrinsic Defects in Silicon Carbide Polytypes. *Materials Science Forum*, **2001**, 353-356, 499-504	0.4	37
60	Ab initio density-functional supercell calculations of hydrogen defects in cubic SiC. *Physical Review B*, **2001**, 63,	3.3	99
59	Silicon antisite in 4H SiC. *Physical Review Letters*, **2001**, 87, 045502	7.4	34
58	The Carbon Vacancy Pair in 4H and 6H SiC. *Materials Science Forum*, **2000**, 338-342, 821-824	0.4	6
57	Fast SiC Epitaxial Growth in a Chimney CVD Reactor and HTCVD Crystal Growth Developments. *Materials Science Forum*, **2000**, 338-342, 131-136	0.4	27
56	Silicon vacancy related defect in 4H and 6H SiC. *Physical Review B*, **2000**, 61, 2613-2620	3.3	202
55	Optically detected cyclotron resonance investigations on 4H and 6H SiC: Band-structure and transport properties. *Physical Review B*, **2000**, 61, 4844-4849	3.3	21
54	Hole effective masses in 4H SiC. *Physical Review B*, **2000**, 61, R10544-R10546	3.3	36
53	Bandstructure and Transport Properties of 4H- and 6H-SiC: Optically Detected Cyclotron Resonance Investigations. *Materials Science Forum*, **2000**, 338-342, 559-562	0.4	1
52	Vacancies and their Complexes with H in SiC. *Materials Science Forum*, **2000**, 338-342, 817-820	0.4	7
51	Vanadium-related Center in 4H Silicon Carbide. *Materials Science Forum*, **2000**, 338-342, 631-634	0.4	2
50	Hole Effective Masses in 4H SiC Determined by Optically Detected Cyclotron Resonance. *Materials Science Forum*, **2000**, 338-342, 563-566	0.4	
49	Deep-level luminescence at 1.0 eV in 6H SiC. *Materials Research Society Symposia Proceedings*, **2000**, 640, 1		2
48	Overcoordinated hydrogens in the carbon vacancy: donor centers of SiC. *Physical Review Letters*, **2000**, 84, 4926-9	7.4	34

47	Configuration transformation of metastable defects in 6H-SiC. *Semiconductor Science and Technology*, **1999**, 14, 251-256	1.8	5
46	Photoluminescence and Zeeman effect in chromium-doped 4H and 6H SiC. *Journal of Applied Physics*, **1999**, 86, 4348-4353	2.5	31
45	Electron-paramagnetic-resonance studies of defects in electron-irradiated p-type 4H and 6H SiC. *Physica B: Condensed Matter*, **1999**, 273-274, 655-658	2.8	8
44	Carbon-vacancy related defects in 4H- and 6H-SiC. *Materials Science and Engineering B: Solid-State Materials for Advanced Technology*, **1999**, 61-62, 202-206	3.1	28
43	Liquid phase epitaxial growth of SiC. *Journal of Crystal Growth*, **1999**, 197, 147-154	1.6	62
42	Observation of negative-U centers in 6H silicon carbide. *Applied Physics Letters*, **1999**, 74, 839-841	3.4	32
41	Optically detected magnetic resonance studies of intrinsic defects in 6H-SiC. *Semiconductor Science and Technology*, **1999**, 14, 1141-1146	1.8	28
40	A Complex Defect Related to the Carbon Vacancy in 4H and 6H SiC. *Physica Scripta*, **1999**, T79, 46	2.6	9
39	Negative-U centers in 4H silicon carbide. *Physical Review B*, **1998**, 58, R10119-R10122	3.3	127
38	Optically Detected Magnetic Resonance Studies of Non-Radiative Recombination Centres in 6H SiC. *Materials Science Forum*, **1998**, 264-268, 599-602	0.4	6
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